## **Application Data Sheet**

# **Application Information**

Application Type:: Regular

Subject Matter:: Utility

Suggested Classification:: 256/287

Suggested Group Art Unit:: 2820

CD-ROM or CD-R? None

Title:: Drain Extended MOS Transistor with Improved

Breakdown Robustness

Attorney Docket Number:: TI-34637

Request for Early Publication?:: No

Request for Non-Publication?:: No

Suggested Drawing Figure:: 3b

Total Drawing Sheets:: 5

Small Entity:: No

Petition included?::

Secrecy Order in Parent Appl.?:: No

#### **Applicant Information**

Applicant Authority type:: Inventor

Primary Citizenship Country: US

Status:: Full Capacity

Given Name:: Sameer

Middle Name:: P.

Family Name:: Pendharkar

City of Residence:: Dallas

State or Province of Residence:: TX

Country of Residence:: US

Street of mailing address:: 7575 Frankford Road

Apt. 3223

City of mailing address::

Dallas

State or Province of mailing address::

TX

Postal or Zip Code of mailing address:: 75252

# **Correspondence Information**

Correspondence Customer Number::

23494

# Representative Information

Representative Customer Number::

23494

TX

### **Assignee Information**

Assignee Name::

Texas Instruments Incorporated

Street of mailing address:: 7839 Churchill Way, MS 3999

City of mailing address:: Dallas

State or Province of mailing address::

Country of mailing address::

Postal or Zip Code of mailing address:: 75251